



80V 3.2mΩ N-Ch Power MOSFET

Features

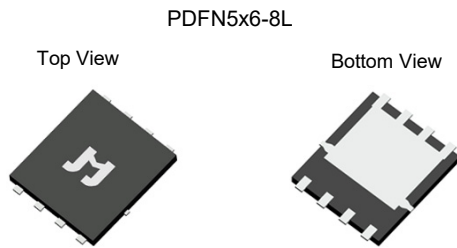
- Ultra-low $R_{DS(ON)}$
- Low Gate Charge
- 100% UIS Tested, 100% R_g Tested
- Pb-free Lead Plating
- Halogen-free and RoHS-compliant

Product Summary

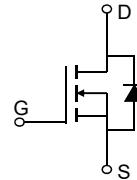
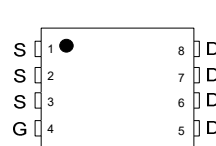
Parameter	Value	Unit
V_{DS}	80	V
$V_{GS(th)}_{Typ}$	3.0	V
I_D (@ $V_{GS} = 10V$) ⁽¹⁾	153	A
$R_{DS(ON)}_{Typ}$ (@ $V_{GS} = 10V$)	3.2	mΩ

Applications

- Power Management in Telecom., Industrial Automation, CE
- Current Switching in DC/DC & AC/DC Sub-systems
- Motor Driving in Power Tool, E-bike



Pin Configuration
Top View

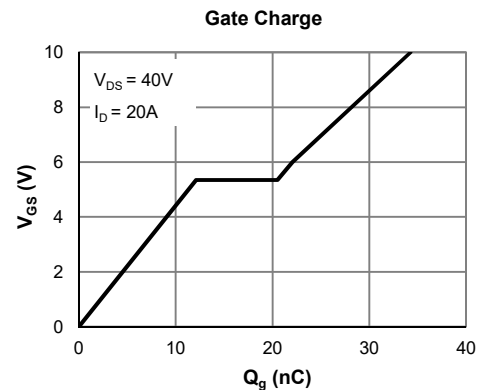
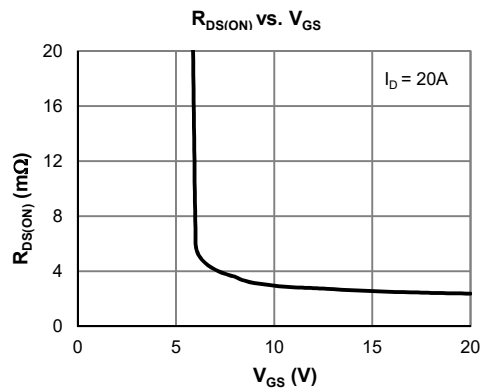


Ordering Information

Device	Package	# of Pins	Marking	MSL	T_J (°C)	Media	Quantity (pcs)
JMSH0803NGS-13	PDFN5x6-8L	8	H0803NS	1	-55 to 150	13-inch Reel	5000

Absolute Maximum Ratings (@ $T_A = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Value	Unit
Drain-to-Source Voltage	V_{DS}	80	V
Gate-to-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current ⁽¹⁾	I_D	$T_C = 25^\circ\text{C}$	153
		$T_C = 100^\circ\text{C}$	97
Pulsed Drain Current ⁽²⁾	I_{DM}	612	A
Avalanche Energy ⁽³⁾	E_{AS}	542	mJ
Power Dissipation ⁽⁴⁾	P_D	$T_C = 25^\circ\text{C}$	178
		$T_C = 100^\circ\text{C}$	71
Junction & Storage Temperature Range	T_J, T_{STG}	-55 to 150	°C



**Electrical Characteristics** (@ $T_J = 25^\circ\text{C}$ unless otherwise specified)

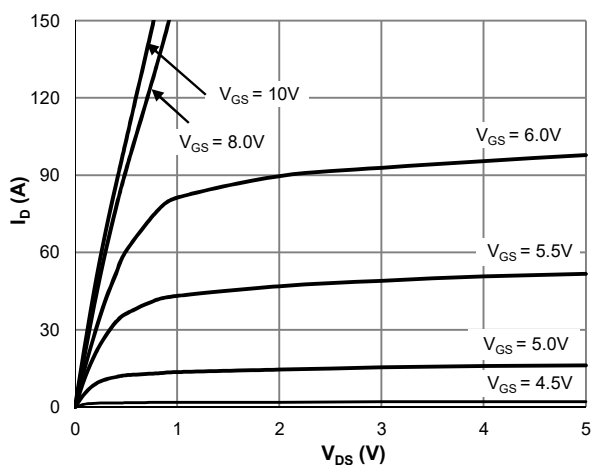
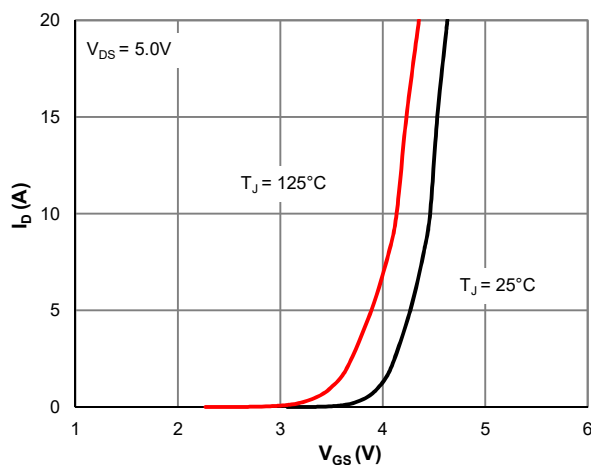
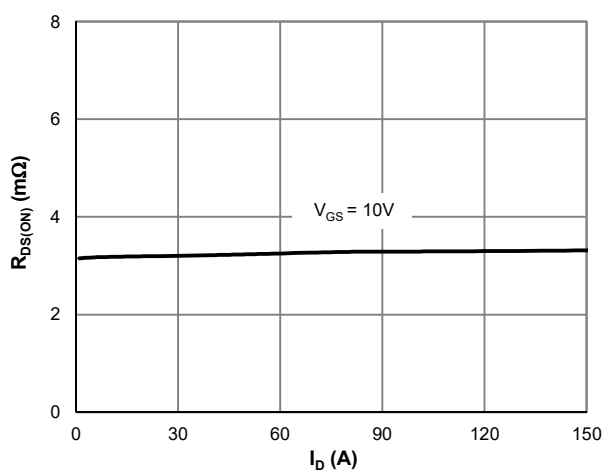
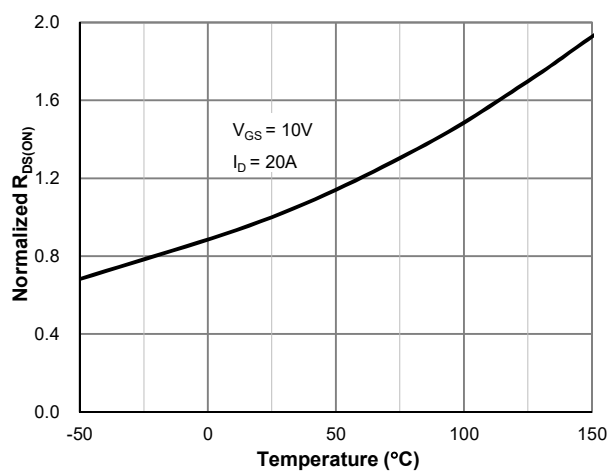
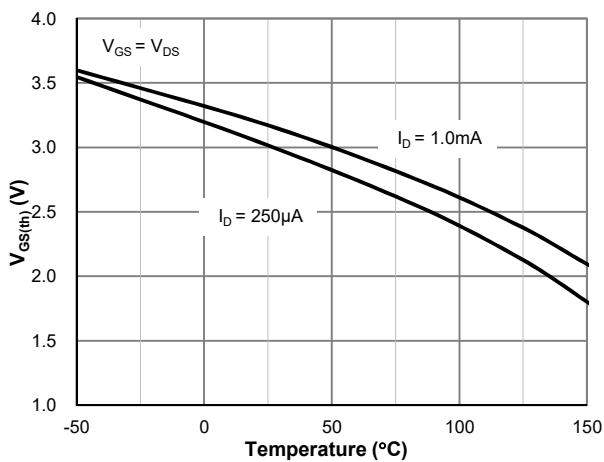
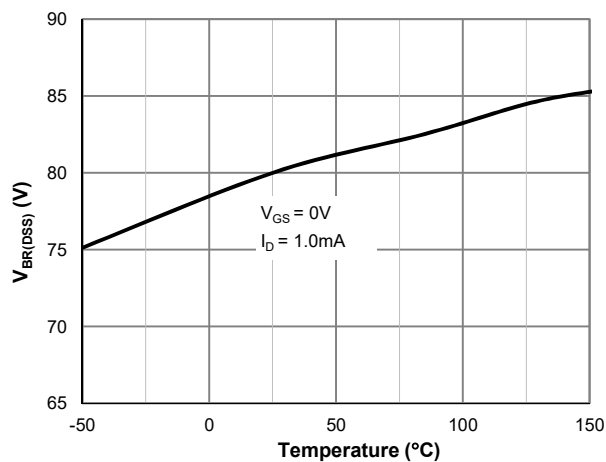
Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
STATIC PARAMETERS						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$I_D = 250\mu\text{A}$, $V_{GS} = 0\text{V}$	80			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 64\text{V}$, $V_{GS} = 0\text{V}$ $T_J = 55^\circ\text{C}$			1.0 5.0	μA
Gate-Body Leakage Current	I_{GSS}	$V_{DS} = 0\text{V}$, $V_{GS} = \pm 20\text{V}$			± 100	nA
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 250\mu\text{A}$	2.0	3.0	4.0	V
Static Drain-Source ON-Resistance	$R_{DS(ON)}$	$V_{GS} = 10\text{V}$, $I_D = 20\text{A}$		3.2	3.9	$\text{m}\Omega$
Forward Transconductance	g_{FS}	$V_{DS} = 5\text{V}$, $I_D = 20\text{A}$		41		S
Diode Forward Voltage	V_{SD}	$I_S = 1\text{A}$, $V_{GS} = 0\text{V}$		0.66	1.0	V
Diode Continuous Current	I_S	$T_C = 25^\circ\text{C}$			153	A
DYNAMIC PARAMETERS ⁽⁵⁾						
Input Capacitance	C_{iss}	$V_{GS} = 0\text{V}$, $V_{DS} = 40\text{V}$, $f = 1\text{MHz}$		2165		pF
Output Capacitance	C_{oss}			1404		pF
Reverse Transfer Capacitance	C_{rss}			31		pF
Gate Resistance	R_g	$V_{GS} = 0\text{V}$, $V_{DS} = 0\text{V}$, $f = 1\text{MHz}$		2.0		Ω
SWITCHING PARAMETERS ⁽⁵⁾						
Total Gate Charge (@ $V_{GS} = 10\text{V}$)	Q_g	$V_{GS} = 0$ to 10V $V_{DS} = 40\text{V}$, $I_D = 20\text{A}$		34		nC
Total Gate Charge (@ $V_{GS} = 6.0\text{V}$)	Q_g			22		nC
Gate Source Charge	Q_{gs}			12.1		nC
Gate Drain Charge	Q_{gd}			8.4		nC
Turn-On DelayTime	$t_{D(on)}$	$V_{GS} = 10\text{V}$, $V_{DS} = 40\text{V}$ $R_L = 2.0\Omega$, $R_{GEN} = 3\Omega$		13.9		ns
Turn-On Rise Time	t_r			26		ns
Turn-Off DelayTime	$t_{D(off)}$			25		ns
Turn-Off Fall Time	t_f			8.5		ns
Body Diode Reverse Recovery Time	t_{rr}	$I_F = 20\text{A}$, $dI_F/dt = 100\text{A}/\mu\text{s}$		61		ns
Body Diode Reverse Recovery Charge	Q_{rr}	$I_F = 20\text{A}$, $dI_F/dt = 100\text{A}/\mu\text{s}$		97		nC

Thermal Performance

Parameter	Symbol	Typ.	Max.	Unit
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	50	60	$^\circ\text{C}/\text{W}$
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	0.70	0.90	$^\circ\text{C}/\text{W}$

Notes:

1. Computed continuous current assumes the condition of T_{J_Max} while the actual continuous current depends on the thermal & electro-mechanical application board design.
2. This single-pulse measurement was taken under $T_{J_Max} = 150^\circ\text{C}$.
3. E_{AS} of 542 mJ is based on starting $T_J = 25^\circ\text{C}$, $L = 3.0\text{mH}$, $I_{AS} = 19\text{A}$, $V_{GS} = 10\text{V}$, $V_{DD} = 40\text{V}$; 100% test at $L = 0.3\text{mH}$, $I_{AS} = 45\text{A}$.
4. The power dissipation P_D is based on $T_{J_Max} = 150^\circ\text{C}$.
5. This value is guaranteed by design hence it is not included in the production test.

Typical Electrical & Thermal Characteristics

Figure 1: Saturation Characteristics

Figure 2: Transfer Characteristics

Figure 3: $R_{DS(ON)}$ vs. Drain Current

Figure 4: $R_{DS(ON)}$ vs. Junction Temperature

Figure 5: $V_{GS(th)}$ vs. Junction Temperature

Figure 6: $V_{BR(DSS)}$ vs. Junction Temperature

Typical Electrical & Thermal Characteristics

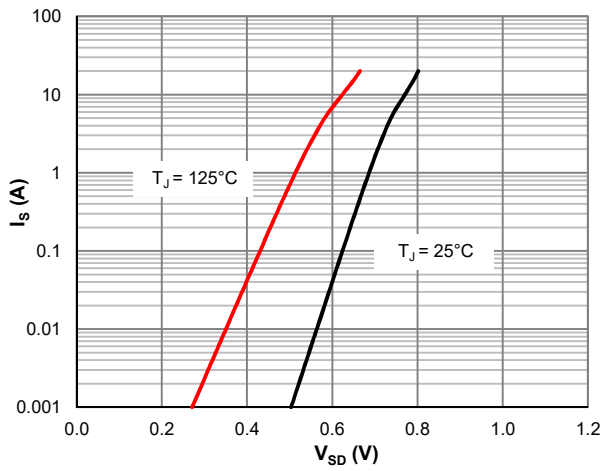


Figure 7: Body-Diode Characteristics

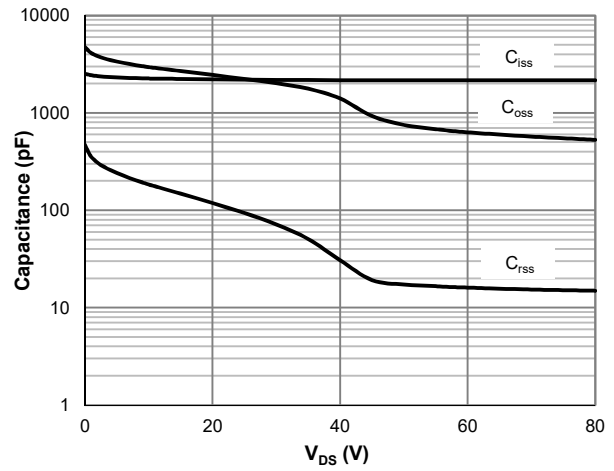


Figure 8: Capacitance Characteristics

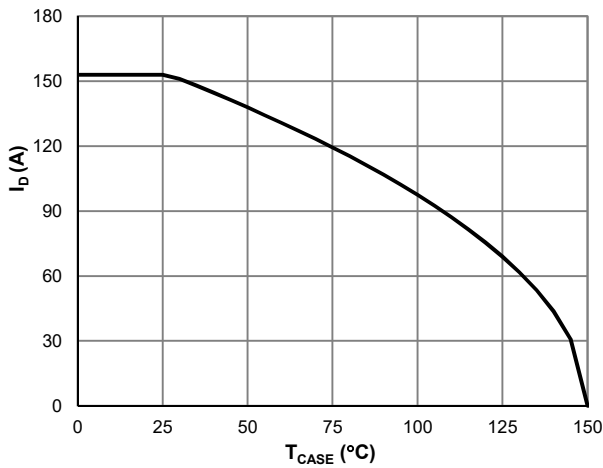


Figure 9: Current De-rating

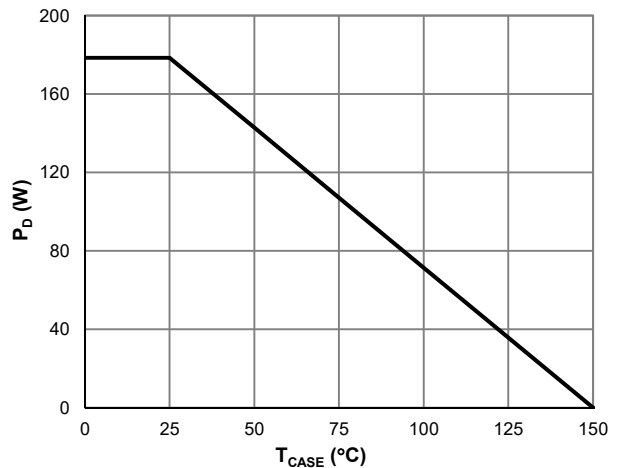


Figure 10: Power De-rating

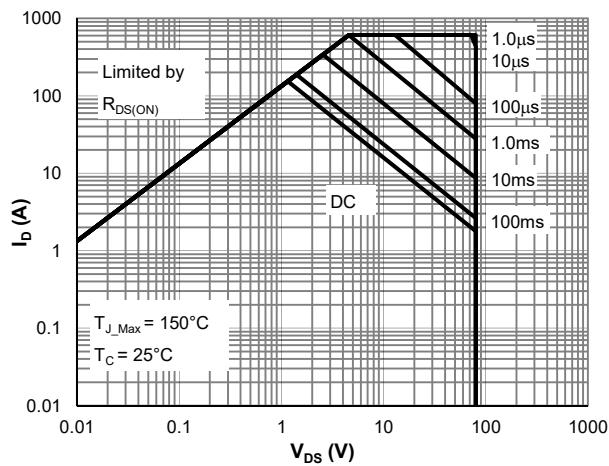


Figure 11: Maximum Safe Operating Area

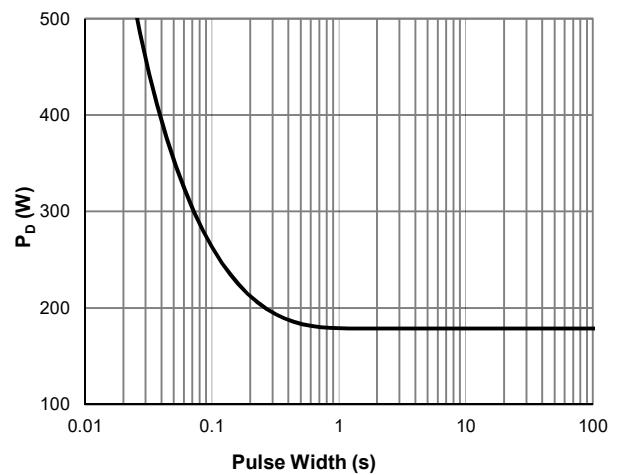


Figure 12: Single Pulse Power Rating, Junction-to-Case



Typical Electrical & Thermal Characteristics

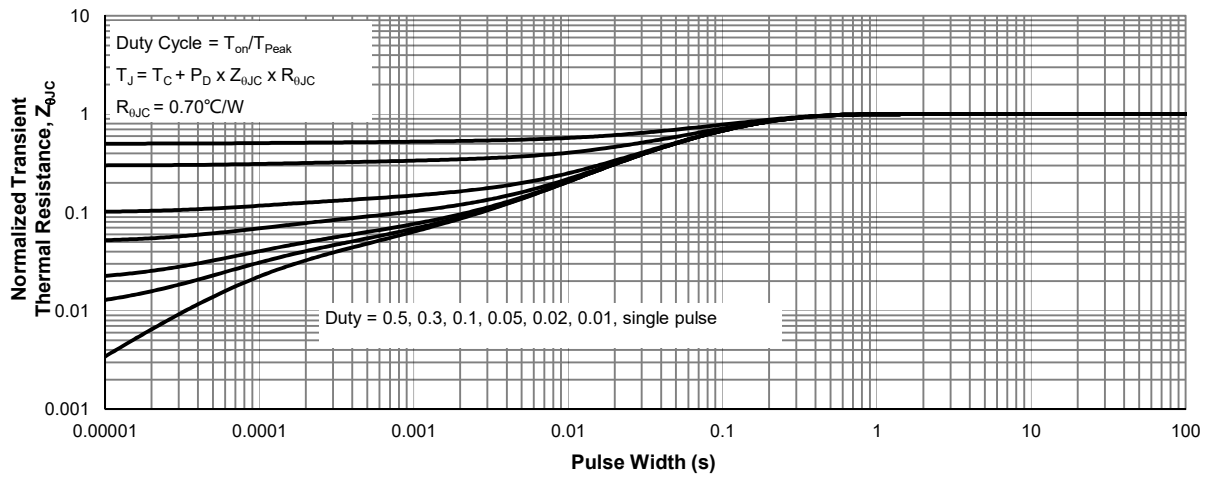
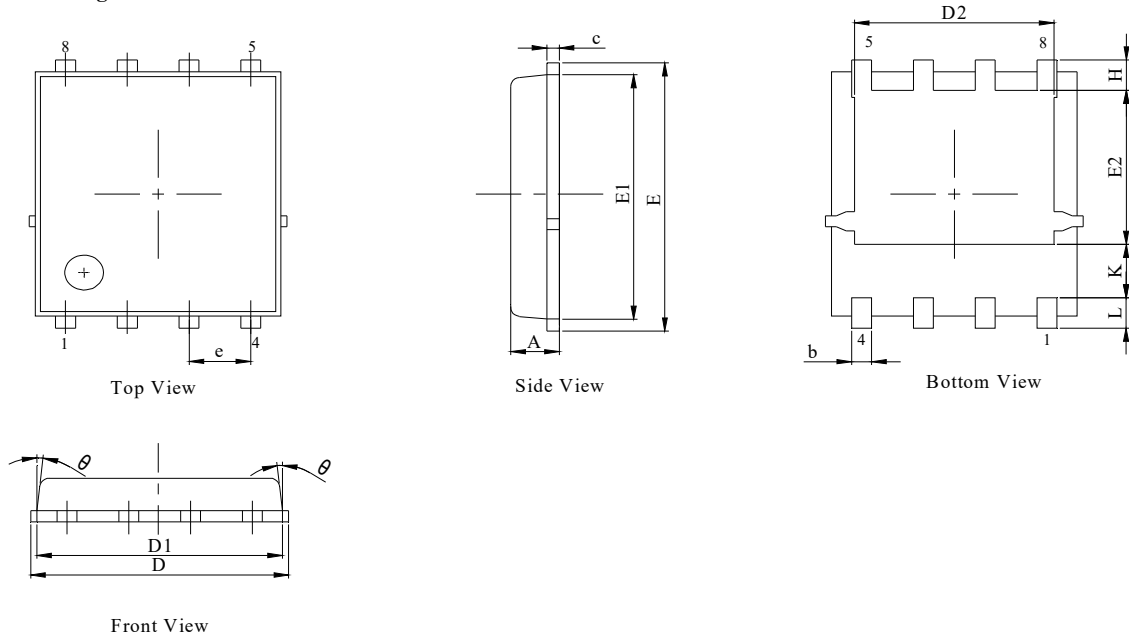
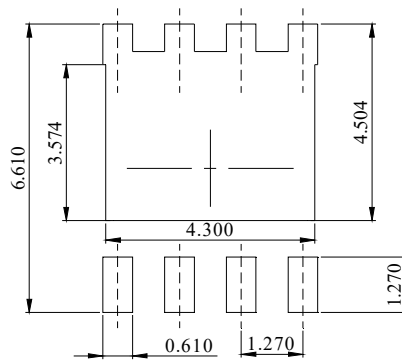


Figure 13: Normalized Maximum Transient Thermal Impedance

PDFN5x6-8L Package Information
Package Outline

NOTES:

1. Dimension and tolerance per ASME Y14.5M, 1994.
2. All dimensions in millimeter (angle in degree).
3. Dimensions $D1$ and $E1$ do not include mold flash protrusions or gate burrs.

DIM.	MILLIMETER		
	MIN.	NOM.	MAX.
A	0.90	1.00	1.10
b	0.31	0.41	0.51
c	0.20	0.25	0.30
D	5.00	5.20	5.40
D1	4.95	5.05	5.15
D2	4.00	4.10	4.20
E	6.05	6.15	6.25
E1	5.50	5.60	5.70
E2	3.42	3.53	3.63
e	1.27BSC		
H	0.60	0.70	0.80
L	0.50	0.70	0.80
K	1.23 REF		
θ	-	-	10°

Recommended Soldering Footprint


DIMENSIONS: MILLIMETERS